

TOSHIBA Photocoupler GaAs IRed & Photo-Transistor

TLP631, TLP632

Programmable Controllers

AC / DC-Input Module

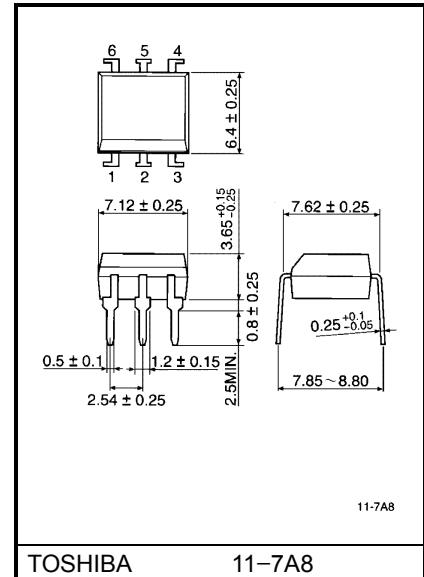
Solid State Relay

The TOSHIBA TLP631 and TLP632 consist of a photo-transistor optically coupled to a gallium arsenide infrared emitting diode in a six lead plastic DIP.

TLP632 is no-base internal connection for high-EMI environments.

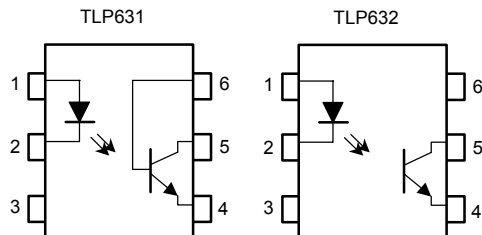
- Collector-emitter voltage: 55 V (min.)
- Current transfer ratio: 50% (min.)
Rank GB: 100% (min.)
- Isolation voltage: 5000V_{rms} (min.)
- UL recognized: UL1577, file no. E67349

Unit in mm



Weight: 0.4 g

Pin Configurations (top view)



1: Anode
2: Cathode
3: N.C.
4: Emitter
5: Collector
6: Base

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Maximum Ratings (Ta = 25°C)

Characteristic		Symbol	Rating	Unit
LED	Forward current	I_F	60	mA
	Forward current derating (Ta ≥ 39°C)	$\Delta I_F / ^\circ\text{C}$	-0.7	mA / °C
	Peak forward current (100µs pulse, 100pps)	I_{FP}	1	A
	Reverse voltage	V_R	5	V
	Junction temperature	T_j	125	°C
Detector	Collector-emitter voltage	V_{CEO}	55	V
	Collector-base voltage (TLP631)	V_{CBO}	80	V
	Emitter-collector voltage	V_{ECO}	7	V
	Emitter-base voltage (TLP631)	V_{EBO}	7	V
	Collector current	I_C	50	mA
	Power dissipation	P_C	150	mW
	Power dissipation derating (Ta ≥ 25°C)	$\Delta P_C / ^\circ\text{C}$	-1.5	mW / °C
	Junction temperature	T_j	125	°C
Storage temperature range		T_{stg}	-55~125	°C
Operating temperature range		T_{opr}	-55~100	°C
Lead soldering temperature (10s)		T_{sol}	260	°C
Total package power dissipation		P_T	250	mW
Total package power dissipation derating (Ta ≥ 25°C)		$\Delta P_T / ^\circ\text{C}$	-2.5	mW / °C
Isolation voltage (AC, 1 min., R.H. ≤ 60%)		BV_S	5000	V_{rms}

Recommended Operating Conditions

Characteristic	Symbol	Min.	Typ.	Max.	Unit
Supply voltage	V_{CC}	—	5	24	V
Forward current	I_F	—	16	25	mA
Collector current	I_C	—	1	10	mA
Operating temperature	T_{opr}	-25	—	85	°C

Individual Electrical Characteristics (Ta = 25°C)

Characteristic		Symbol	Test Condition	Min.	Typ.	Max.	Unit
LED	Forward voltage	V_F	$I_F = 10 \text{ mA}$	1.0	1.15	1.3	V
	Reverse current	I_R	$V_R = 5 \text{ V}$	—	—	10	μA
	Capacitance	C_T	$V = 0, f = 1 \text{ MHz}$	—	30	—	pF
Detector	Collector–emitter breakdown voltage	$V_{(BR) \text{ CEO}}$	$I_C = 0.5 \text{ mA}$	55	—	—	V
	Emitter–collector breakdown voltage	$V_{(BR) \text{ ECO}}$	$I_E = 0.1 \text{ mA}$	7	—	—	V
	Collector–base breakdown voltage (TLP631)	$V_{(BR) \text{ CBO}}$	$I_C = 0.1 \text{ mA}$	80	—	—	V
	Emitter–base breakdown voltage (TLP631)	$V_{(BR) \text{ EBO}}$	$I_E = 0.1 \text{ mA}$	7	—	—	V
	Collector dark current	I_{CEO}	$V_{\text{CE}} = 24 \text{ V}$	—	10	100	nA
			$V_{\text{CE}} = 24 \text{ V}, T_a = 85^\circ\text{C}$	—	2	50	μA
	Capacitance collector to emitter	C_{CE}	$V = 0, f = 1 \text{ MHz}$	—	10	—	pF

Coupled Electrical Characteristics (Ta = 25°C)

Characteristic	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Current transfer ratio	I_C / I_F	$I_F = 5 \text{ mA}, V_{\text{CE}} = 5 \text{ V}$ Rank GB	50	—	600	%
			100	—	600	
Saturated CTR	$I_C / I_F (\text{sat})$	$I_F = 1 \text{ mA}, V_{\text{CE}} = 0.4 \text{ V}$ Rank GB	—	60	—	%
			30	—	—	
Collector–emitter saturation voltage	$V_{\text{CE}} (\text{sat})$	$I_C = 2.4 \text{ mA}, I_F = 8 \text{ mA}$	—	—	0.4	V

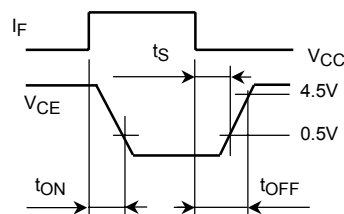
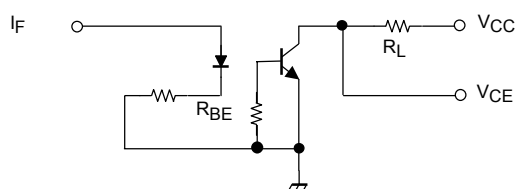
Isolation Characteristics (Ta = 25°C)

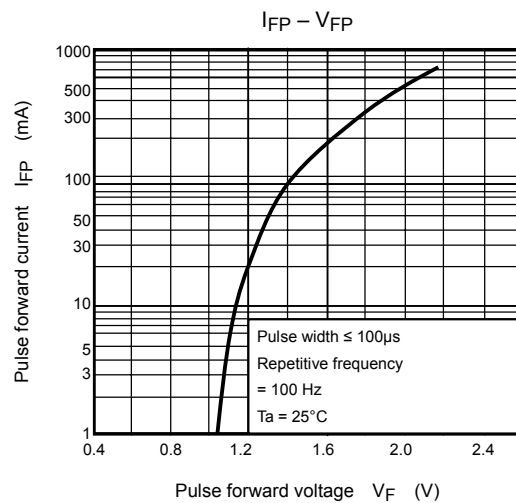
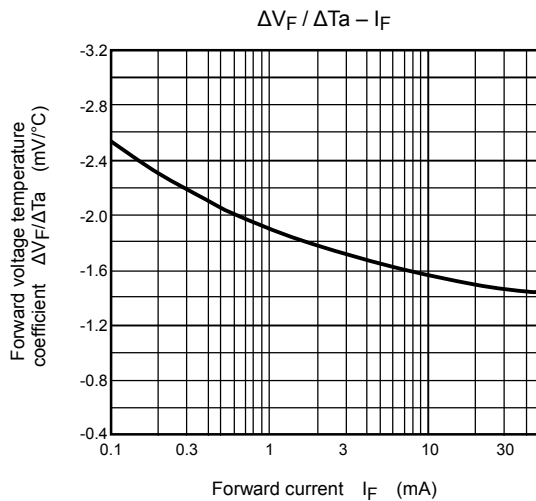
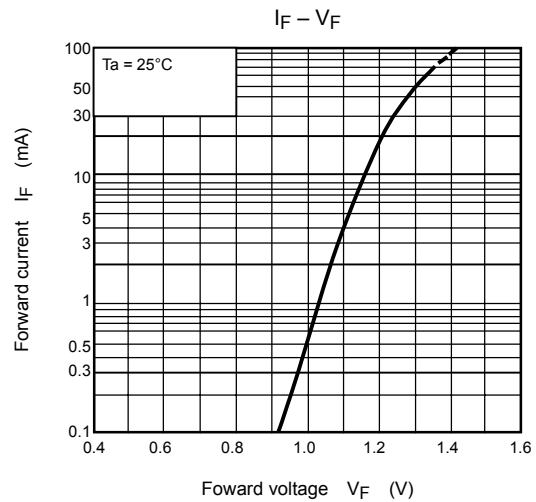
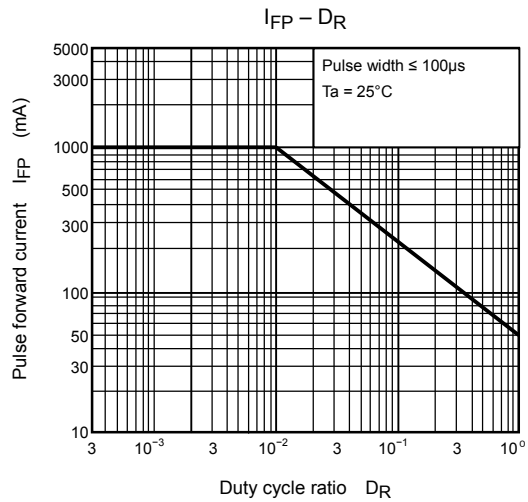
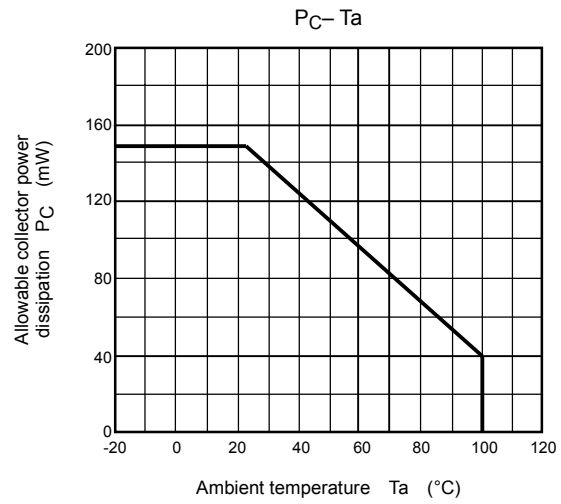
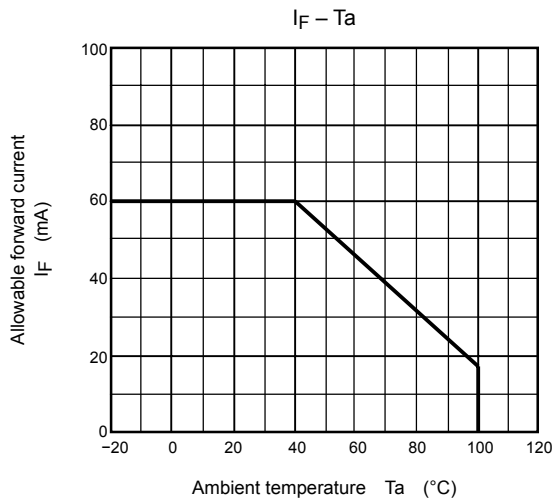
Characteristic	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Capacitance (input to output)	C_S	$V_S = 0, f = 1 \text{ MHz}$	—	0.8	—	pF
Isolation resistance	R_S	$V_S = 500 \text{ V}, \text{R.H.} \leq 60\%$	5×10^{10}	10^{14}	—	Ω
Isolation voltage	BV_S	AC, 1 minute	5000	—	—	V_{rms}
		AC, 1 second, in oil	—	10000	—	
		DC, 1 minute, in oil	—	10000	—	V_{dc}

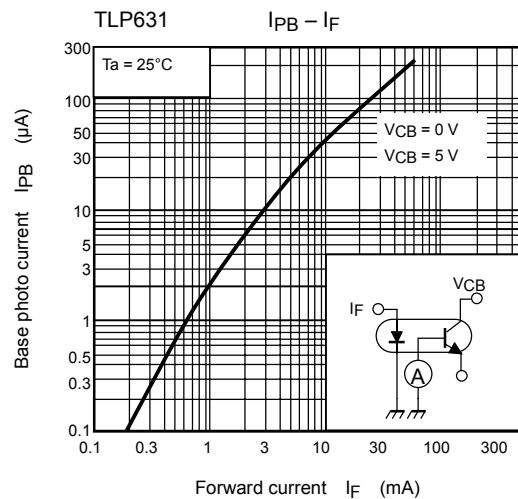
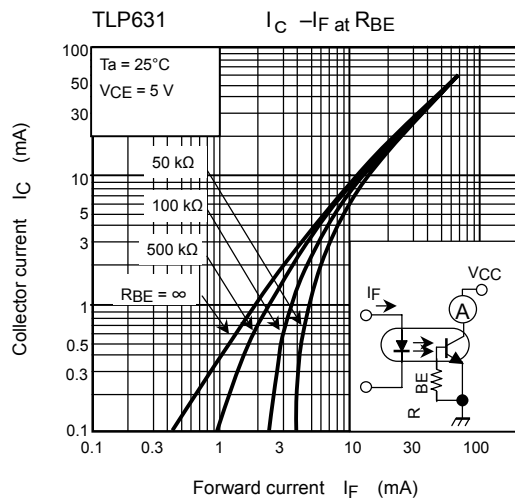
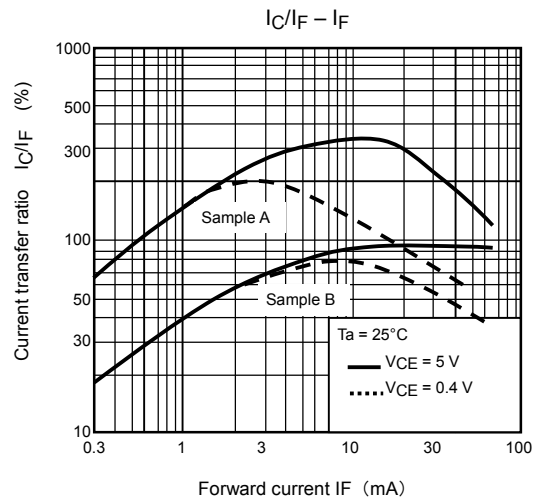
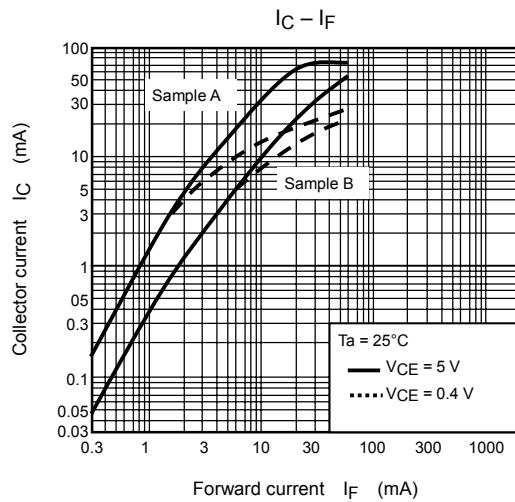
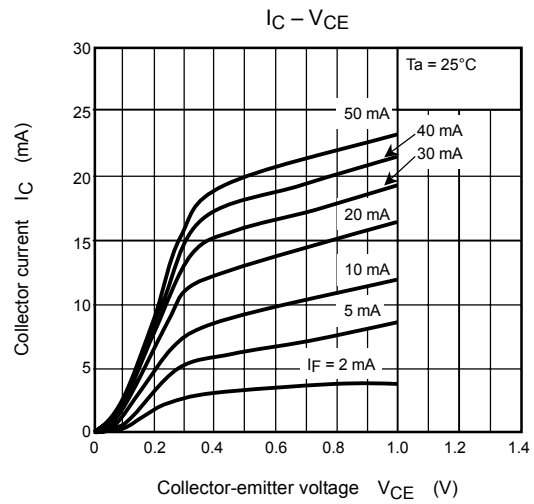
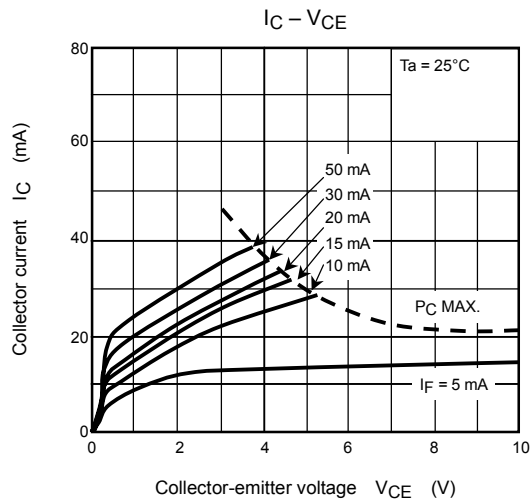
Switching Characteristics (Ta = 25°C)

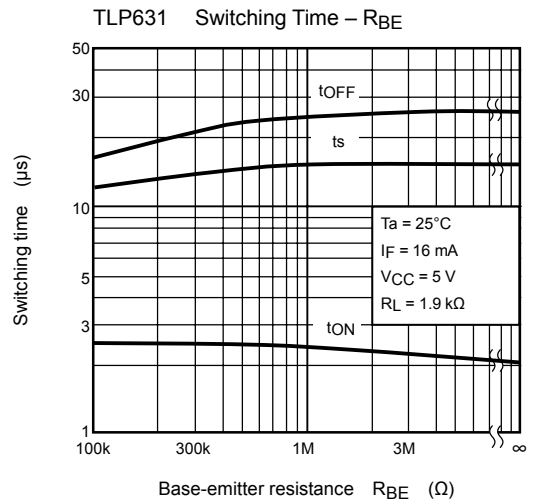
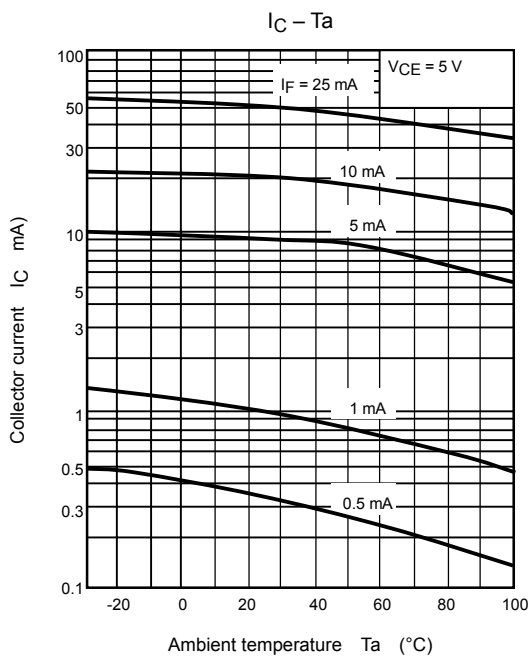
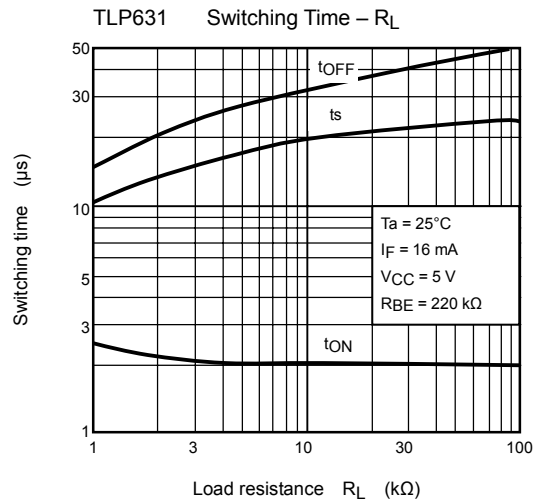
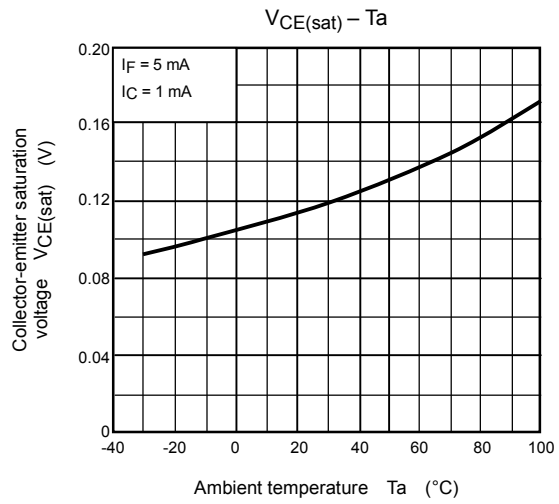
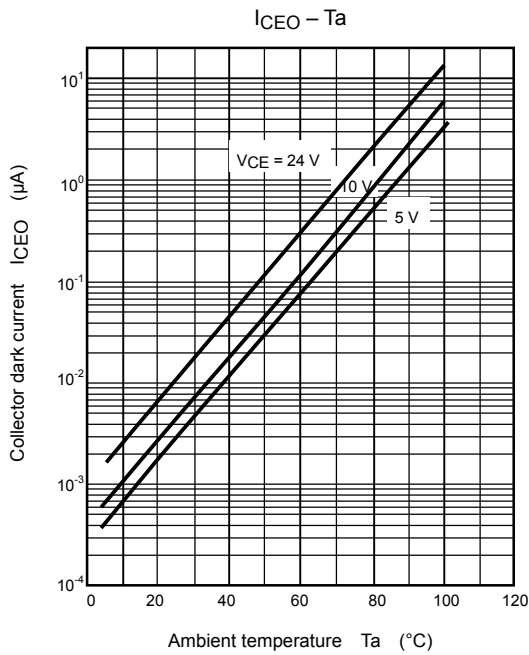
Characteristic	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Rise time	t_r	$V_{CC} = 10 \text{ V}, I_C = 2 \text{ mA}$ $R_L = 100 \Omega$	—	2	—	μs
Fall time	t_f		—	3	—	
Turn-on time	t_{on}		—	3	—	
Turn-off time	t_{off}		—	3	—	
Turn-on time	t_{ON}	$R_L = 1.9 \text{ k}\Omega$ (Fig.1) $R_{BE} = \text{OPEN}$ $V_{CC} = 5 \text{ V}, I_F = 16 \text{ mA}$	—	2	—	μs
Storage time	t_s		—	15	—	
Turn-off time	t_{OFF}		—	25	—	
Turn-on time	t_{ON}	$R_L = 1.9 \text{ k}\Omega$ (Fig.1) $R_{BE} = 220 \text{ k}\Omega$ (TLP631) $V_{CC} = 5 \text{ V}, I_F = 16 \text{ mA}$	—	2	—	μs
Storage time	t_s		—	12	—	
Turn-off time	t_{OFF}		—	20	—	

Fig. 1 Switching time test circuit









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